

MOSFET – Power, Single, N-Channel

40 V, 106 A, 3.3 mΩ

NTMFS5H431NL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter			Value	Unit
V _{DSS}	Drain-to-Source Voltage			40	V
V _{GS}	Gate-to-Source Voltage			±20	V
I _D	Continuous Drain Current R _{θJC} (Notes 1, 3)	Steady State	T _C = 25°C	106	A
			T _C = 100°C	67	
P _D	Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	66	W
			T _C = 100°C	26	
I _D	Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	23	A
			T _A = 100°C	14	
P _D	Power Dissipation R _{θJA} (Notes 1, 2)		T _A = 25°C	3.0	W
			T _A = 100°C	1.2	
I _{DM}	Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		600	A
T _J , T _{stg}	Operating Junction and Storage Temperature Range			-55 to +150	°C
I _S	Source Current (Body Diode)			55	A
E _{AS}	Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 8.5 A)			280	mJ
T _L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C

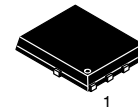
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

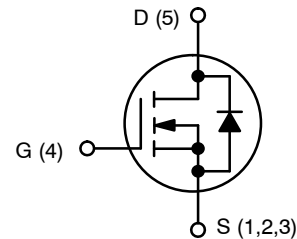
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State	1.9	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	41	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	3.3 mΩ @ 10 V	106 A
	5 mΩ @ 4.5 V	

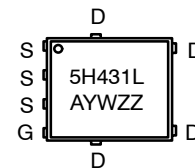


DFN5
(SO-8FL)
CASE 488AA
STYLE 1



N-CHANNEL MOSFET

MARKING DIAGRAM



5H431L = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NTMFS5H431NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{(BR)DSS}/T_J$	Drain-to-Source Breakdown Voltage Temperature Coefficient			15.8		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		250	
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.0	V
$V_{GS(TH)}/T_J$	Threshold Temperature Coefficient			-4.6		mV/°C
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		2.8	3.3	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		4.0	5	
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		70		S

CHARGES AND CAPACITANCES

C_{ISS}	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$		1730		pF
C_{OSS}	Output Capacitance			400		
C_{RSS}	Reverse Transfer Capacitance			25		
Q_{OSS}	Output Charge	$V_{GS} = 0\text{ V}, V_{DD} = 20\text{ V}$		20		nC
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 20\text{ A}$		28		nC
$Q_{G(TH)}$	Threshold Gate Charge	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}; I_D = 20\text{ A}$		13		
Q_{GS}	Gate-to-Source Charge			3		
Q_{GD}	Gate-to-Drain Charge			5.6		
Q_{GP}	Plateau Voltage			3.4		
V_{GP}	Plateau Voltage			3		V

SWITCHING CHARACTERISTICS (Note 5)

$t_{d(ON)}$	Turn-On Delay Time	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 20\text{ A}, R_G = 2.5\text{ }\Omega$		17		ns
t_r	Rise Time			55		
$t_{d(OFF)}$	Turn-Off Delay Time			45		
t_f	Fall Time			14		

DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Forward Diode Voltage	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.8	1.2	V
			T _J = 125°C		0.65		
t _{RR}	Reverse Recovery Time	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 20 A			31		ns
t _a	Charge Time				16		
t _b	Discharge Time				15		
Q _{RR}	Reverse Recovery Charge					22	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.



TYPICAL CHARACTERISTICS

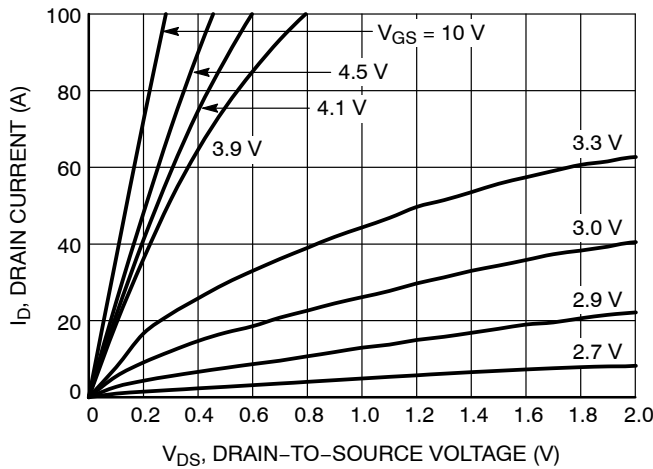


Figure 1. On-Region Characteristics

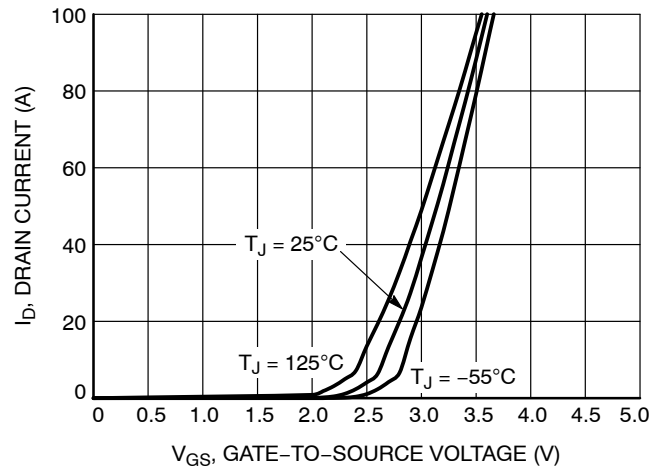


Figure 2. Transfer Characteristics

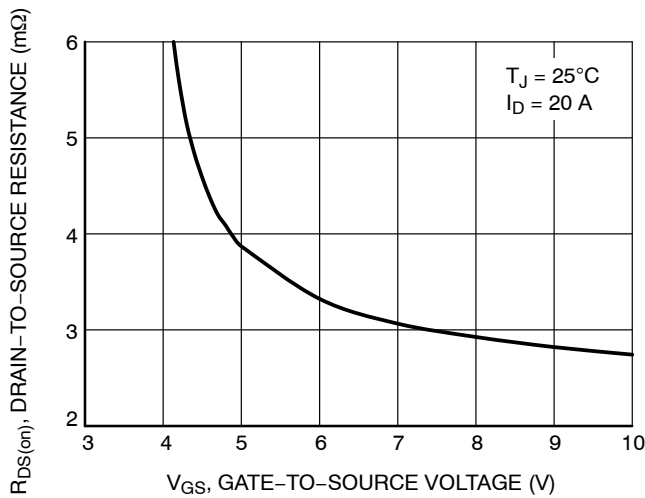


Figure 3. On-Resistance vs. Gate-to-Source Voltage

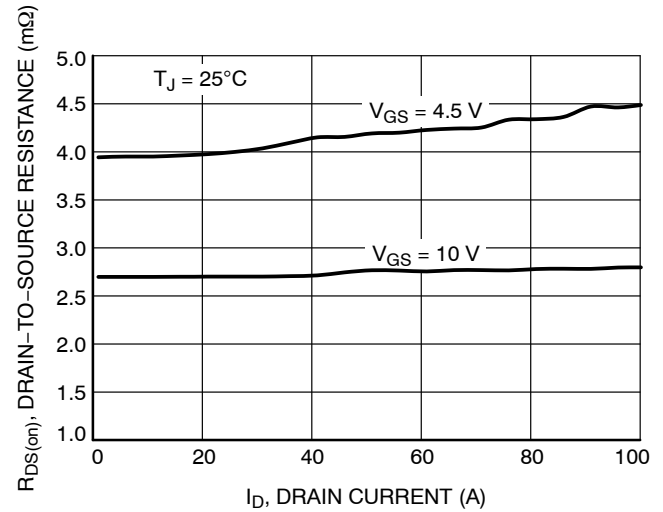


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

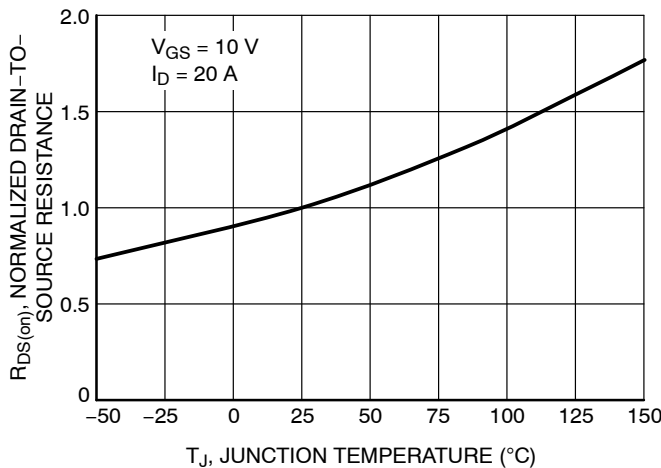


Figure 5. On-Resistance Variation with Temperature

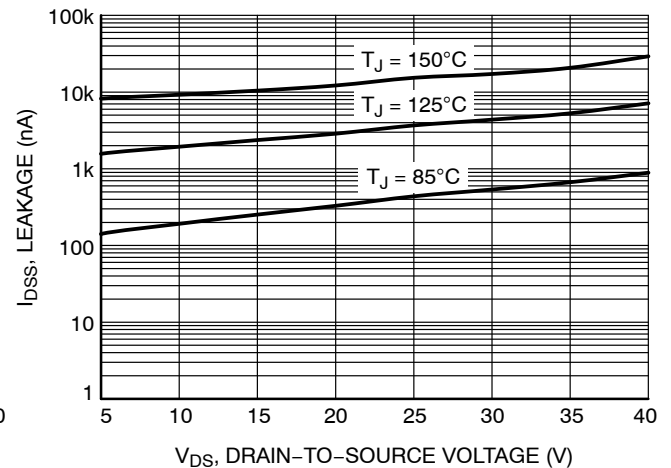


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

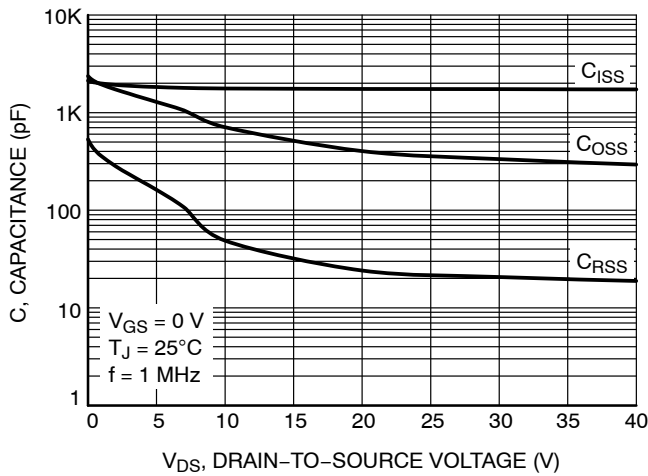


Figure 7. Capacitance Variation

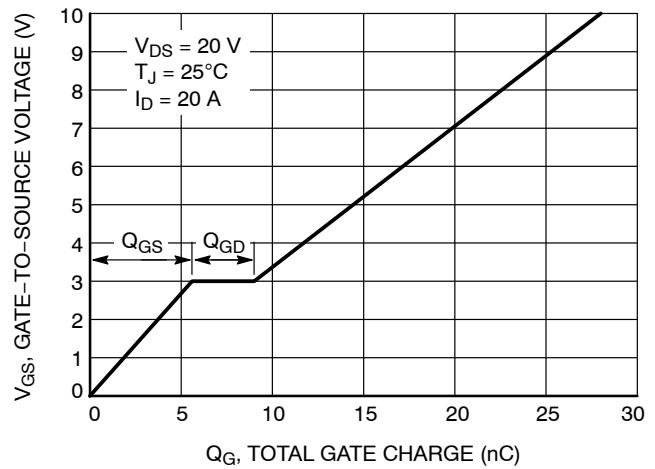


Figure 8. Gate-to-Source vs. Total Charge

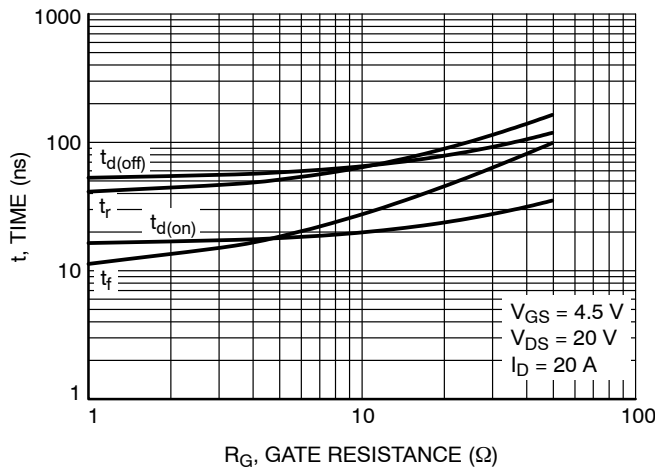


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

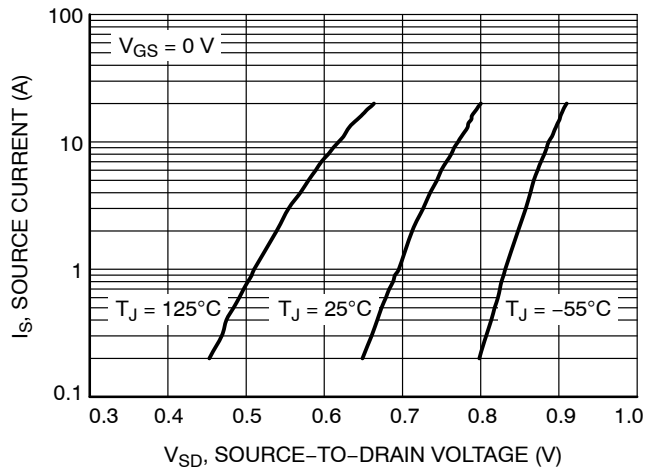


Figure 10. Diode Forward Voltage vs. Current

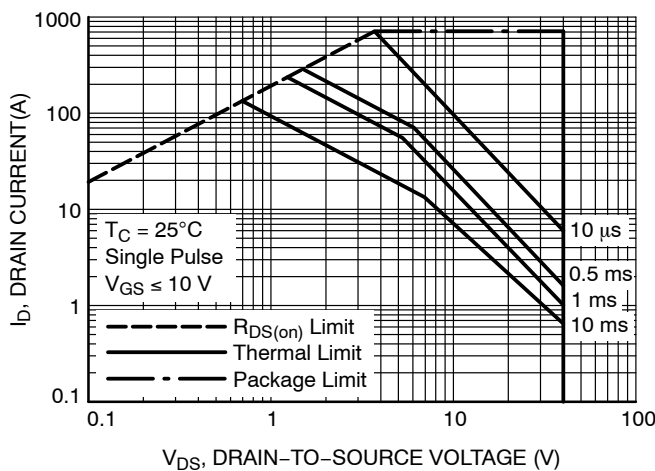


Figure 11. Maximum Rated Forward Biased Safe Operating Area

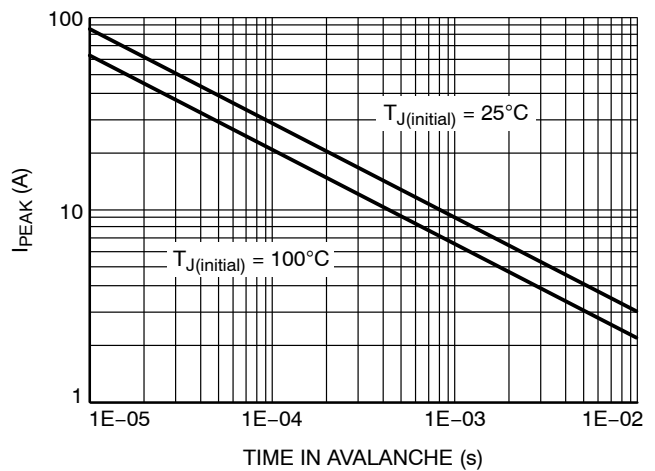


Figure 12. I_{PEAK} vs. Time in Avalanche

NTMFS5H431NL

TYPICAL CHARACTERISTICS (continued)

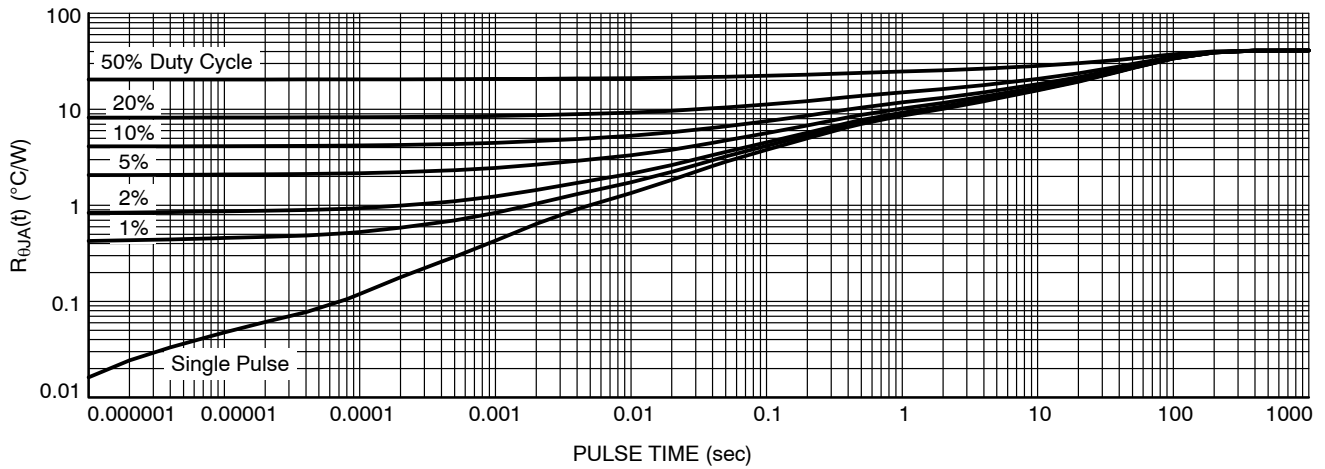


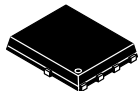
Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMFS5H431NLT1G	5H431L	DFN5 (Pb-Free)	1,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).





1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

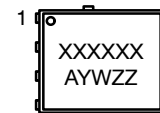
DATE 25 JUN 2018

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

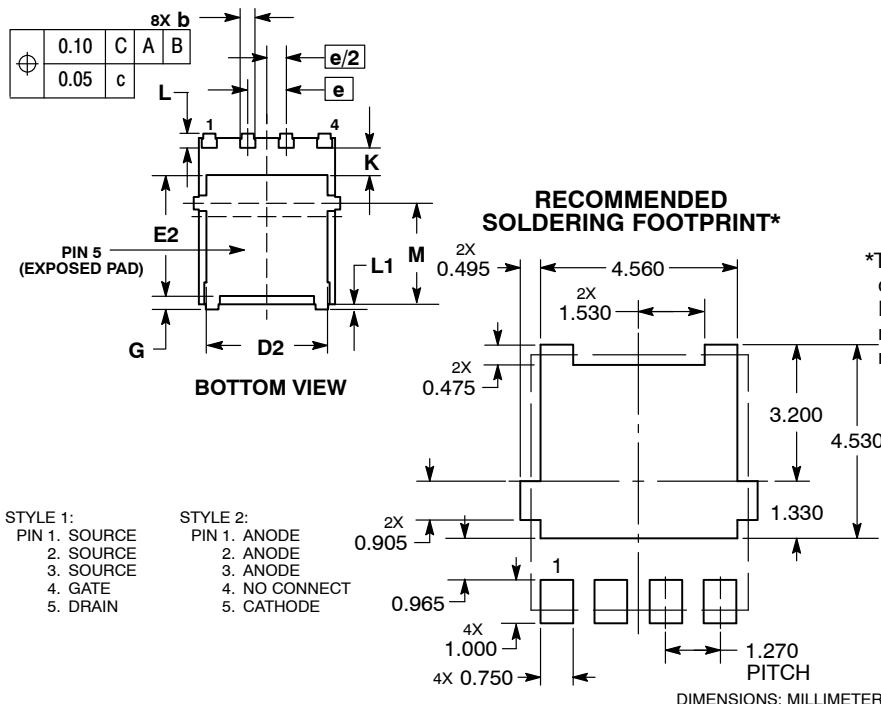
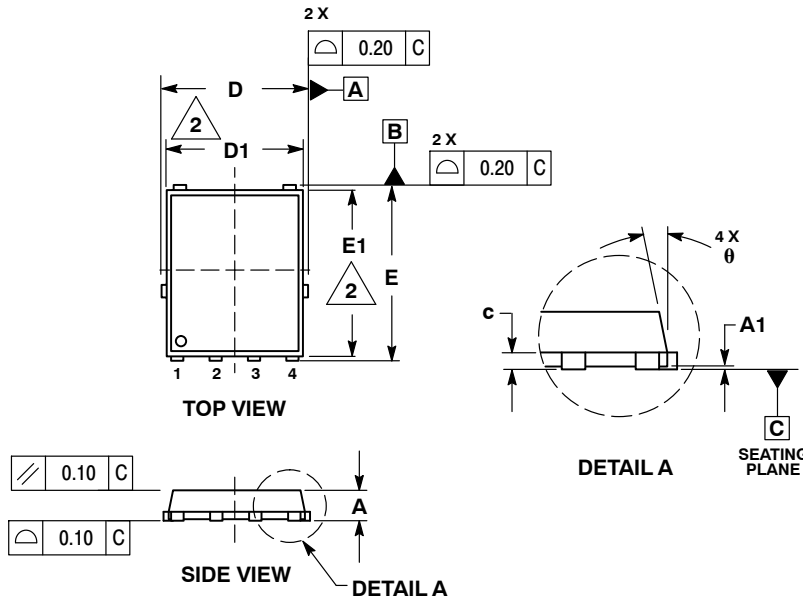
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



STYLE 1:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN

STYLE 2:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. NO CONNECT
 5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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